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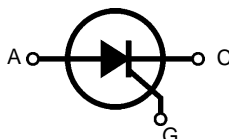
sales@integrated-circuit.com

IXYS **CS 45**

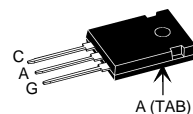
Phase Control Thyristor

V_{RRM} = 800-1600 V
I_{T(RMS)} = 75 A
I_{T(AV)M} = 48 A

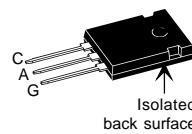
V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
900	800	CS 45-08io1
1300	1200	CS 45-12io1
1700	1600	CS 45-16io1 CS 45-16io1R



TO-247 AD
Version io1



ISOPLUS 247™
Version io1R



* Patent pending

C = Cathode, A = Anode, G = Gate

Symbol	Conditions	Maximum Ratings	
I _{T(RMS)}	T _{VJ} = T _{VJM}	75	A
I _{T(AV)M}	T _C = 75°C; 180° sine	48	A
I _{TSM}	T _{VJ} = 45°C V _R = 0 V	t = 10 ms (50 Hz), sine	520 A
		t = 8.3 ms (60 Hz), sine	560 A
I ² t	T _{VJ} = 45°C V _R = 0 V	t = 10 ms (50 Hz), sine	1350 A ² s
		t = 8.3 ms (60 Hz), sine	1300 A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 μs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/μs	repetitive, I _T = 40 A	150 A/μs
		non repetitive, I _T = I _{T(AV)M}	500 A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000 V/μs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{T(AV)M}	t _p = 30 μs	10 W
		t _p = 300 μs	5 W
P _{G(AV)}			0.5 W
V _{RGM}			10 V
T _{VJ}		-40...+140	°C
T _{VJM}		140	°C
T _{stg}		-40...+125	°C
M _d	Version io1: mounting torque M3	0.8...1.2	Nm
F _C	Version io1R: mounting force with clip	20...120	N
V _{ISOL} *	50/60 Hz, RMS, t = 1 minute, leads-to-tab	2500	V~
Weight		6	g

Features

- Thyristor for line frequency
- International standard package JEDEC TO-247
- Planar passivated chip
- Long-term stability of blocking currents and voltages
- Version AR isolated and UL registered E153432
- Epoxy meets UL 94V-0

Applications

- Motor control
- Power converter
- AC power controller
- Switch-mode and resonant mode power supplies
- Light and temperature control

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Space and weight savings
- Simple mounting
- Improved temperature and power cycling

* Verson io1R only

Symbol	Conditions	Characteristic Values
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 80$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.64 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85 V
r_T		11 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 1.5 V
	$T_{VJ} = -40^\circ\text{C}$	≤ 1.6 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 100 mA
	$T_{VJ} = -40^\circ\text{C}$	≤ 200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	≤ 0.2 V
I_{GD}		≤ 10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10$ μs $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 150 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 2 μs
R_{thJC}	DC current	0.62 K/W
R_{thJH}	DC current	0.82 K/W
a	Max. acceleration, 50 Hz	50 m/s ²

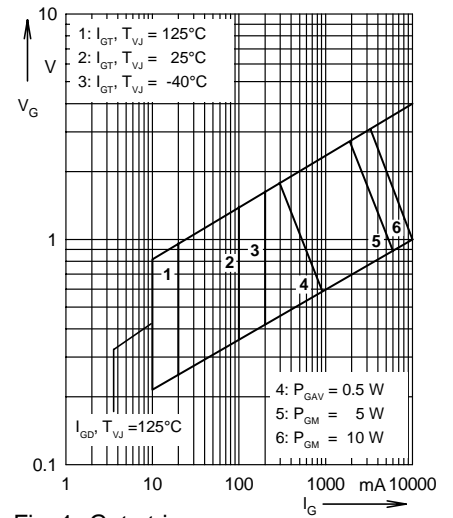


Fig. 1 Gate trigger range

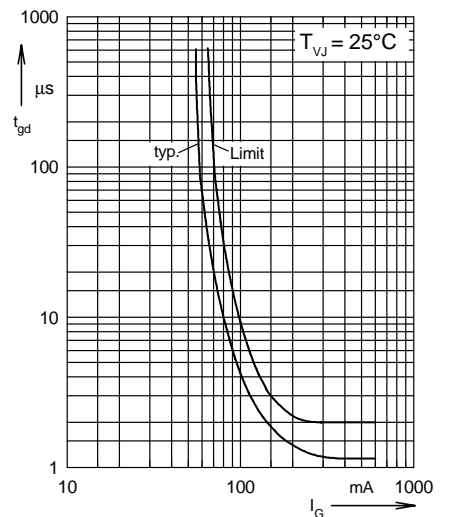


Fig. 2 Gate controlled delay time t_{gd}

TO-247 AD and ISOPLUS 247™

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D*	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

* ISOPLUS 247™ without hole

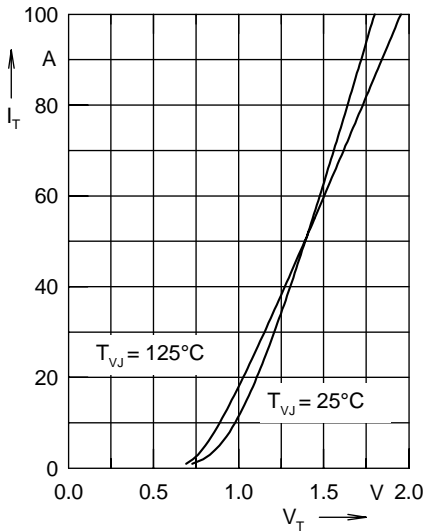


Fig. 3 Forward characteristics

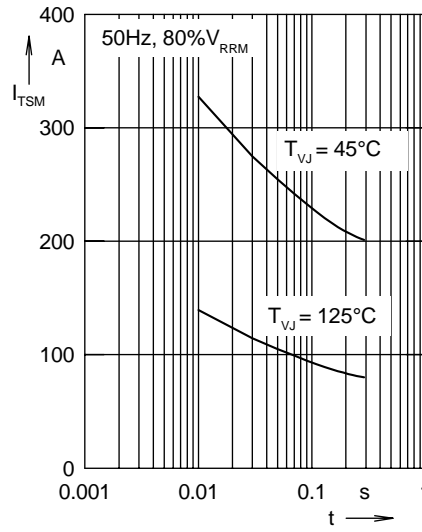


Fig. 4 Surge overload current
 I_{TSM} : crest value, t: duration

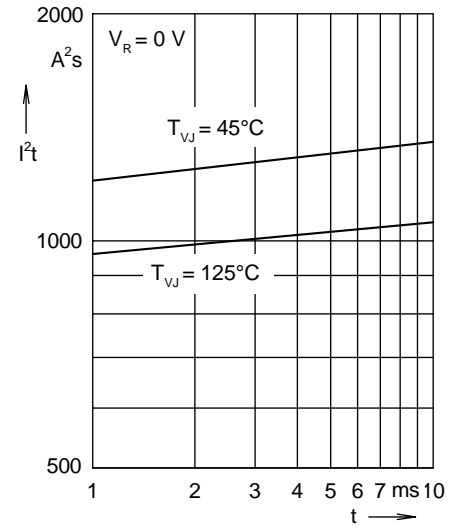


Fig. 5 I^2t versus time (1-10 ms)

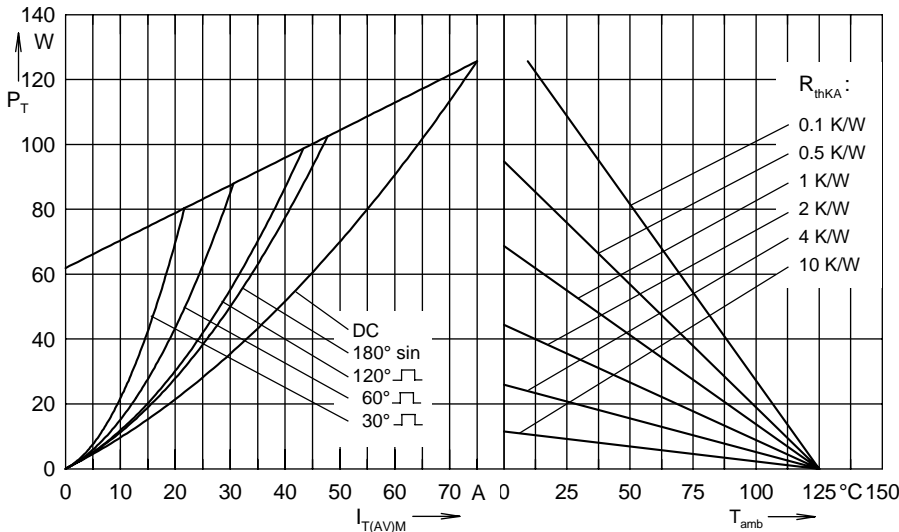


Fig. 6 Power dissipation versus forward current and ambient temperature

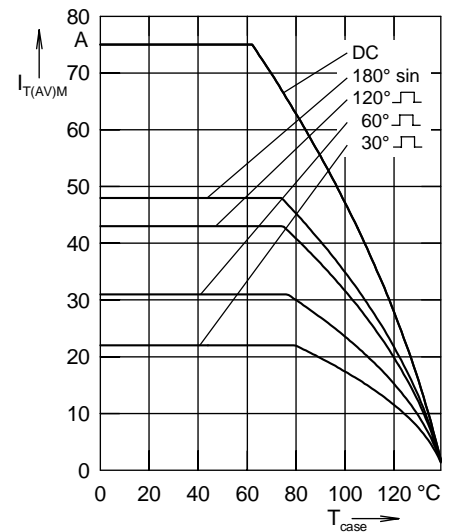


Fig. 7 Max. forward current at case temperature

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.62
180°	0.71
120°	0.748
60°	0.793
30°	0.817

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.206	0.013
2	0.362	0.118
3	0.052	1.488

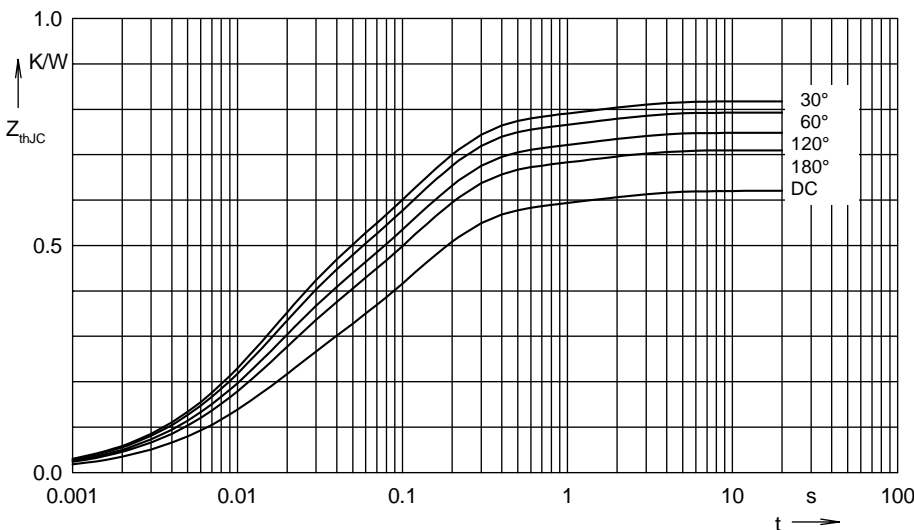


Fig. 8 Transient thermal impedance junction to case